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Inclosure Material:	
Metal	
Overall Length:	
0.505 inches	
Overall Diameter:	
0.650 inches	
End Application:	
General application electronics (gen-ap-e)	
Mounting Facility Quantity:	
1	
Internal Configuration:	
Junction contact	
Electrode Internally-electrically Connected To Case:	
Collector	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed case	
Overall Width Across Flats:	
0.562 inches	
Thread Size:	
0.250 inches	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
100.0 breakover voltage, dc	
Current Rating Per Characteristic:	
18.00 amperes collector current, dc	
Power Rating Per Characteristic:	
0.5 watts peak gate power dissipation	
Maximum Operating Tempurature Per Measurement Point:	
125.0 degrees celsius junction	
Special Features:	
Internal junction configuration arrangement pnpn	
Thread Series Designator:	
Unf	
Terminal Type And Quantity:	
1 threaded stud and 2 tab, solder lug	
Specification Data:	
80131-release3681 professional/industrial association specification	
Shelf Life:	
N/a	

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Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0